

PSMN1R7-30YL

N-channel 30 V 1.7 m Ω logic level MOSFET in LFPAK

Rev. 1 — 30 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power convertors
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2		-	-	109	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 ^{\circ}\text{C}; \text{see } \frac{\text{Figure } 13}{\text{ Composition}}$		-	-	2.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}$		-	1.3	1.7	mΩ
Dynamic cl	naracteristics						
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	8.7	-	nC



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$Q_{G(tot)} \\$	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	36.2	-	nC
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} &V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;} \\ &I_D = 100 \text{ A; } V_{sup} \leq 30 \text{ V;} \\ &R_{GS} = 50 \Omega; \text{ unclamped} \end{split}$	-	-	241	mJ

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	D D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R7-30YL	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		9 , (
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V_{DSM}	peak drain-source voltage	$t_p \le 25 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 360 \text{ nJ};$ pulsed	-	35	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}Ω$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1] -	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1] -	100	Α
I_{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	790	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	109	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
Is	source current	T _{mb} = 25 °C	[1] -	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	790	Α
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped	-	241	mJ

[1] Continuous current is limited by package.

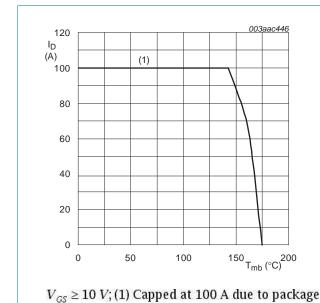


Fig 1. Continuous drain current as a function of mounting base temperature

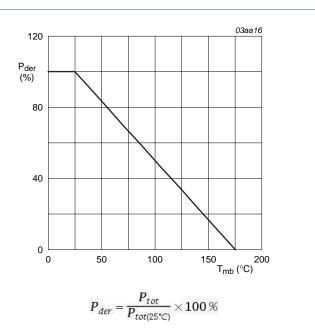
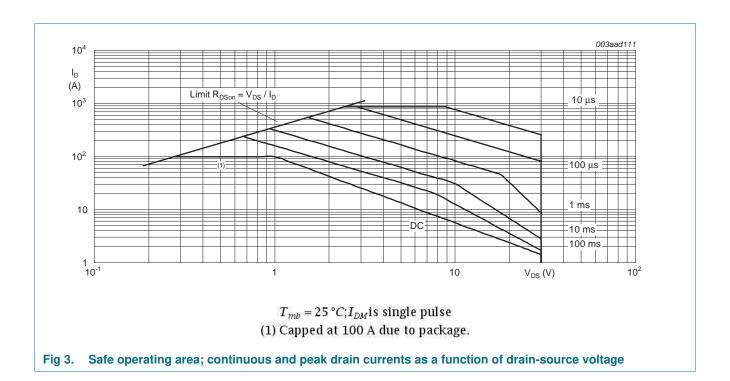


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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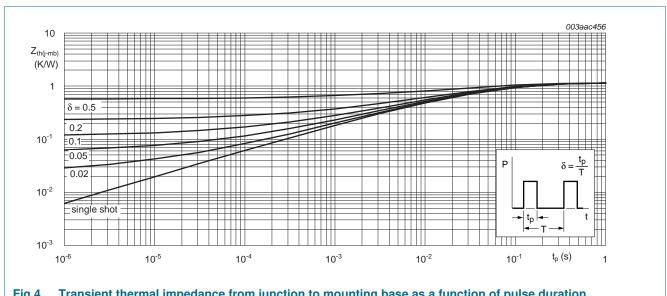
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Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.5	1.1	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
V _{GS(th)} gate-source threshold voltage	-	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	1.3	1.7	2.15	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 150 °C; see Figure 12	0.65	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; see <u>Figure 12</u>	-	-	2.45	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	1.8	2.1	mΩ
resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 150 \text{ °C};$ see <u>Figure 13</u>	-	-	2.8	mΩ	
	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 13	-	-	2.4	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	1.3	1.7	mΩ
R_{G}	gate resistance	f = 1 MHz	-	0.77	1.5	Ω
Dynamic ch	aracteristics					
Q _{G(tot)} total gate charge	total gate charge	$I_D = 10 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	77.9	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	70	-	nC
		$I_D = 10 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 14	-	36.2	-	nC
Q _{GS}	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	11.6	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	8	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	3.6	-	nC
Q_{GD}	gate-drain charge		-	8.7	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.34	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	5057	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	1082	-	pF
C _{rss}	reverse transfer capacitance		-	398	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	46	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	72	-	ns
t _{d(off)}	turn-off delay time		-	76	-	ns
t _f	fall time		_	34	_	ns

 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Source-drain	Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.78	1.2	V	
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A}/\mu s$;	-	45	-	ns	
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	56	-	nC	

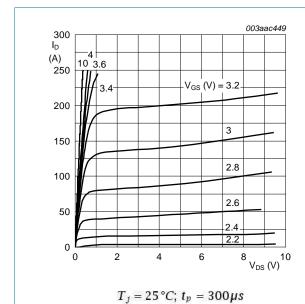
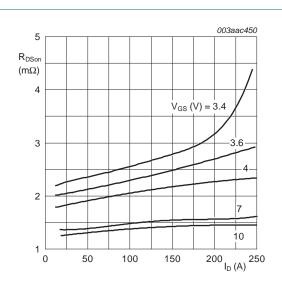


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_j = 25 \,^{\circ}C; t_p = 300 \,\mu s$

Fig 6. Drain-source on-state resistance as a function of drain current; typical values

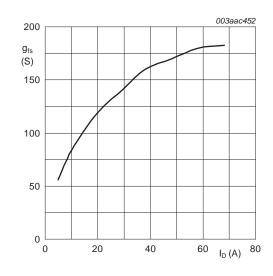
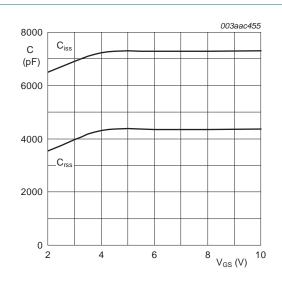


Fig 7. Forward transconductance as a function of drain current; typical values

 $T_j = 25 \,^{\circ}C; V_{DS} = 15 V$



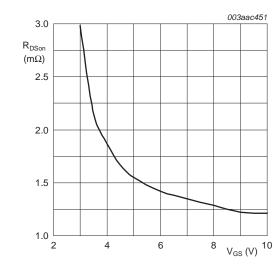
 $V_{DS} = 0V; f = 1MHz$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

PSMN1R7-30YL

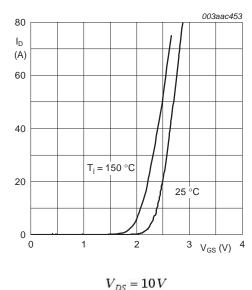
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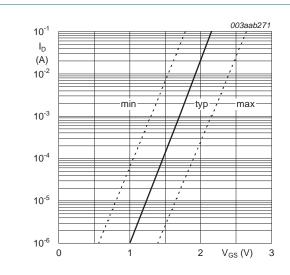
 $T_j = 25\,^{\circ}C; I_D = 15A$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



· DS IO ·

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25 \,{}^{\circ}C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage

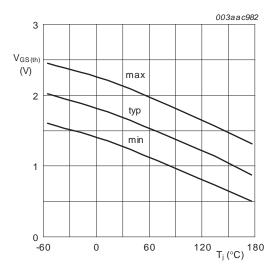


Fig 12. Gate-source threshold voltage as a function of junction temperature

 $I_D = 1 mA; V_{DS} = V_{GS}$

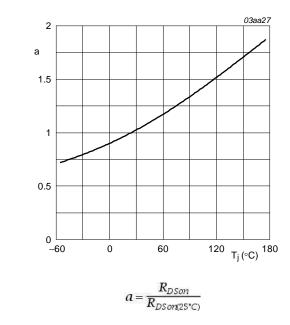


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

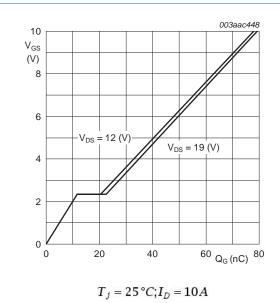


Fig 15. Gate-source voltage as a function of gate charge; typical values

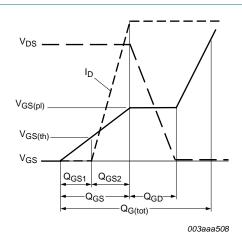
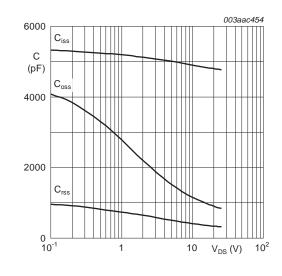


Fig 14. Gate charge waveform definitions



 $V_{GS}=0\,V; f=1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

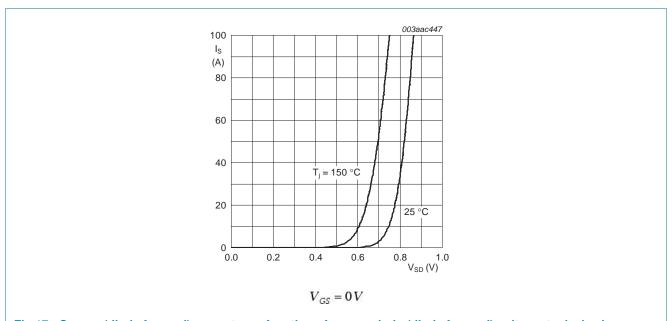
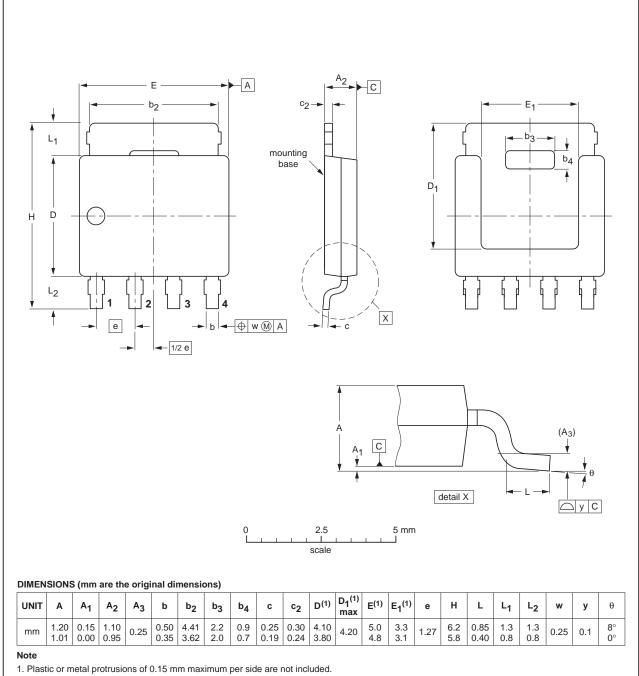


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

Package outline

Plastic single-ended surface-mounted package (LFPAK; Power-SO8); 4 leads

SOT669



OUTLINE	REFERENCES			REFERENCES EUROF		ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT669		MO-235				-06-03-16- 11-03-25

Fig 18. Package outline SOT669 (LFPAK; Power-SO8)

PSMN1R7-30YL

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R7-30YL v.5	20110530	Product data sheet	-	PSMN1R7-30YL v.4
Modifications: • Various changes to content.				
PSMN1R7-30YL v.4	20100420	Product data sheet	-	PSMN1R7-30YL v.3

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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PSMN1R7-30YL

Nexperia

N-channel 30 V 1.7 mΩ logic level MOSFET in LFPAK

11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data1
2	Pinning information
3	Ordering information2
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history12
9	Legal information13
9.1	Data sheet status
9.2	Definitions13
9.3	Disclaimers
9.4	Trademarks14
10	Contact information 14